
QT-Brightek Opto-Coupler Series

6-PIN DIP Phototransistor Optocoupler

Part No.: 4N2X 4N3X H11AX Series



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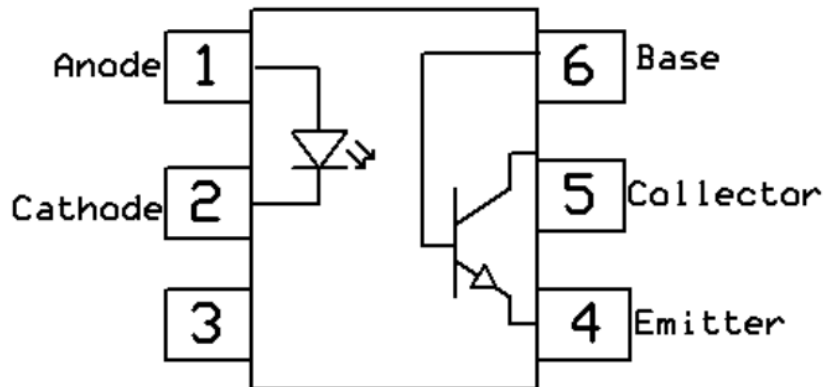
Introduction

Feature:

- 4N2X: 4N25, 4N26, 4N27, 4N28
- 4N3X: 4N35, 4N36, 4N37, 4N38
- H11AX: H11A1, H11A2, H11A3, H11A4, H11A5
- High Isolation voltage (Viso = 5000 VRMS)
- Operating Temperature up to 100 °C
- Meet all JEDEC specifications
- Available in standard DIP, Gullwing, and surface mount lead bend options.
- Conventional black housing package

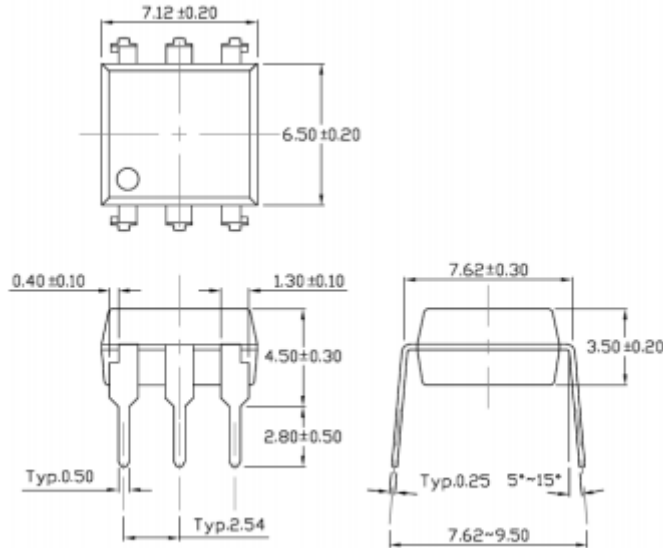
Certification & Compliance:

- Pb free and RoHS Compliant
- UL recognized (File #E338132)
- VDE recognized

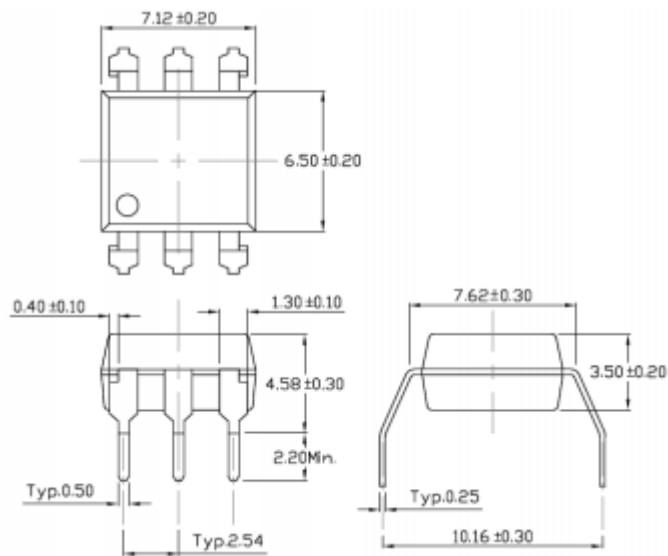
**Schematic:**

Dimension: (Dot location indicates pin 1)

6-Pin DIP Through Hole (Standard):

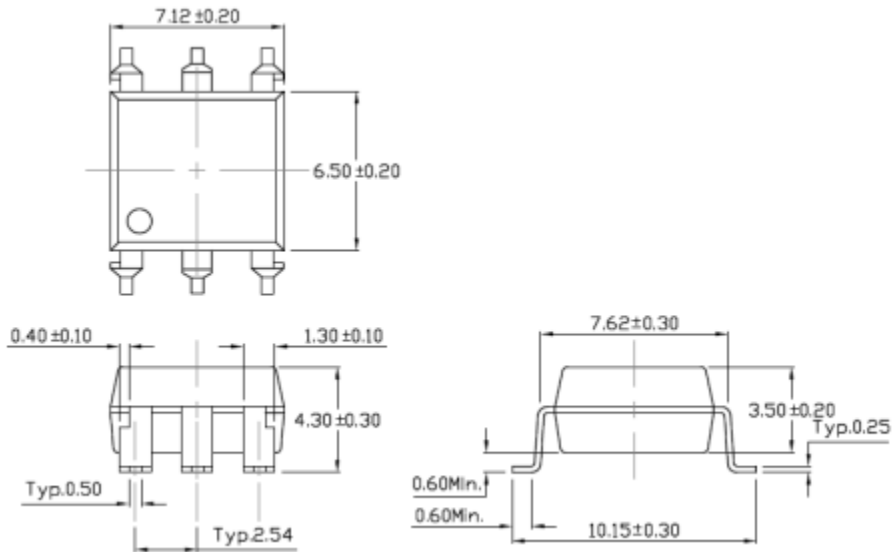


Gullwing Lead Bend Through Hole (Option M):

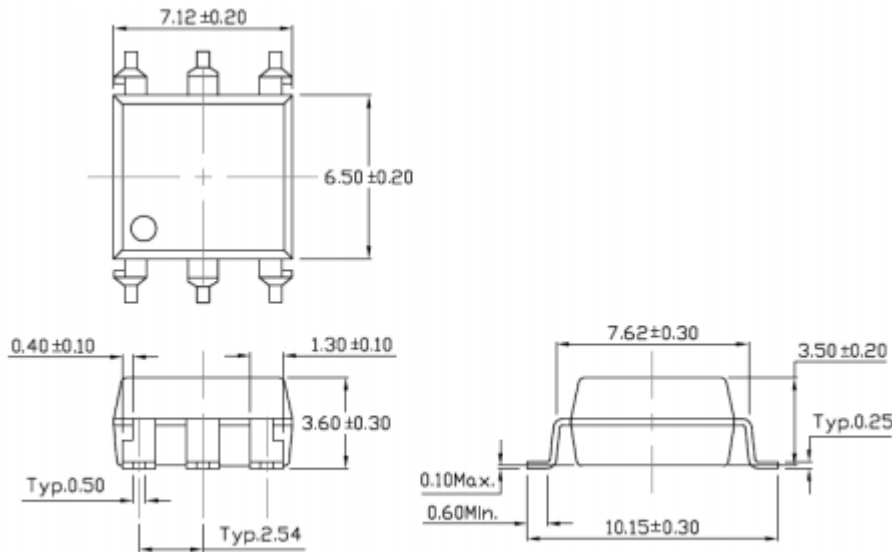


All dimensions are in mm

SMD Lead Bend (Option S):



SMD (Low Profile) Bend (Option SL):



All Dimensions are in mm

Absolute Maximum Rating

Symbol	Parameter	Rating	Units
T_{STG}	Storage Temperature	-55 ~ +150	°C
T_{OPR}	Operating Temperature	-55 ~ +110	°C
T_{SOL}	Lead Solder Temperature	260	°C
V_{ISO}	Isolation voltage	5000	V_{RMS}
EMITTER			
I_F	Continuous Forward Current	60	mA
I_{PF}	Peak Forward Current (300us pulse, $\leq 1 \mu s$ P.W)	1	A
V_R	Reverse Voltage	6	V
P_D	Power Dissipation	100	mW
DETECTOR			
B_{VCEO}	Collector-Emitter Breakdown Voltage	80	V
B_{VEBO}	Collector-Base Breakdown Voltage	80	V
B_{VECO}	Emitter-Collector Breakdown Voltage	7	V
B_{VEBO}	Emitter-Base Breakdown Voltage	7	V
P_D	Power Dissipation	150	mW

Electrical Characteristic: (Ta=25°C)
Emitter

Symbol	Characteristic	Device	Test Condition	Range			Unit
				Min	Typ	Max	
V _F	Forward voltage	4N2X 4N3X H11AX	I _F =10mA	-	1.24	1.4	V
I _R	Reverse current		V _R =6V	-	-	5	μA
C _{IN}	Input Capacitance		F=1MHz	-	45	-	pF

Detector

Symbol	Characteristic	Device	Test Condition	Range			Unit
				Min	Typ	Max	
B _{VCEO}	Collector-Emitter Breakdown voltage	4N2X 4N3X H11AX	I _C =0.1mA	80	-	-	V
B _{VECO}	Emitter-Collector Breakdown		I _E =0.1mA	7	-	-	V
B _{VCBO}	Collector-Base Breakdown		I _C =0.1mA	80	-	-	V
B _{VEBO}	Emitter-Base Breakdown voltage		I _E =0.1mA	7	-	-	V
I _{CEO}	Collector-Emitter Dark current	4N25, 4N26, 4N27, 4N28 H11A1, H11A2, H11A3, H11A4, H11A5	V _{CE} =10V, I _F =0mA	-	-	50	nA
		4N35, 4N36, 4N37, 4N38	V _{CE} =60V, I _F =0mA	-	-	50	nA
I _{CBO}	Collector-Base Dark Current	4N2X, 4N3X, H11AX	V _{CB} =10V, I _F =0mA	-	-	20	nA

DC Transfer Characteristic

Symbol	Characteristic	Device	Test Condition	Range			Unit
				Min	Typ	Max	
CTR	Current Transfer Ratio	4N35, 4N36, 4N37	$I_F=10\text{mA}$, $V_{CE}=10\text{V}$	100	-	-	%
		4N25, 4N26, 4N38, H11A2, H11A3		20	-	-	
		4N27, 4N28, H11A4		10	-	-	
		H11A1		50	-	-	
		H11A5		30	-	-	
$V_{CE(Sat)}$	Collector-Emitter Saturation Voltage	4N25, 4N26, 4N27, 4N28	$I_F=50\text{mA}$, $I_C=2\text{mA}$	-	-	0.5	V
		4N35, 4N36, 4N37	$I_F=10\text{mA}$, $I_C=0.5\text{mA}$	-	-	0.3	
		H11A1, H11A2, H11A3, H11A4, H11A5		-	-	0.4	
		4N38		$I_F=20\text{mA}$, $I_C=4\text{mA}$	-	-	
R_{IO}	Isolation Resistance	4N2X, 4N3X, H11AX	$V_{IO}=500\text{VDC}$	1×10^{11}			Ω
C_{IO}	Isolation Capacitance	4N2X, 4N3X, H11AX	$f=1\text{MHz}$	-	0.25	-	pF

AC Switching Characteristics

Symbol	Characteristic	Device	Test Condition	Range			Unit
				Min	Typ	Max	
T_{on}	Turn on time	4N25, 4N26, 4N27, 4N28, H11A1, H11A2, H11A3, H11A4, H11A5	$I_F=10\text{mA}$, $V_{CC}=10\text{V}$, $R_L=100\Omega$	-	4.3	9.8	μs
		4N35, 4N36, 4N37, 4N38	$I_C=2\text{mA}$, $V_{CC}=10\text{V}$, $R_L=100\Omega$	-	9.8	11.5	
T_{off}	Turn off time	4N25, 4N26, 4N27, 4N28 H11A1, H11A2, H11A3, H11A4 H11A5	$V_{CC}=10\text{V}$, $I_C=10\text{mA}$, $R_L=100\Omega$	-	3.9	9.8	μs
		4N35, 4N36, 4N37, 4N38	$V_{CC}=10\text{V}$, $I_C=10\text{mA}$, $R_L=100\Omega$	-	6.9	11.5	

Characteristic Curves

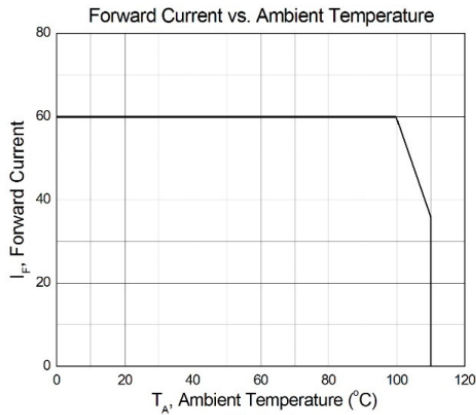


Figure 1

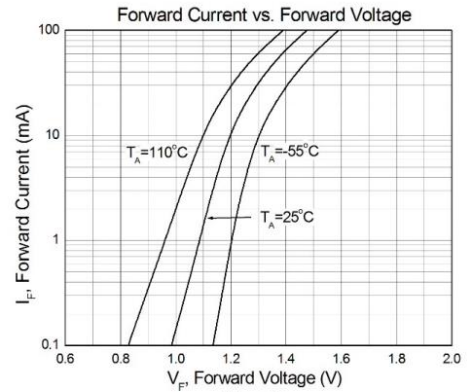


Figure 2

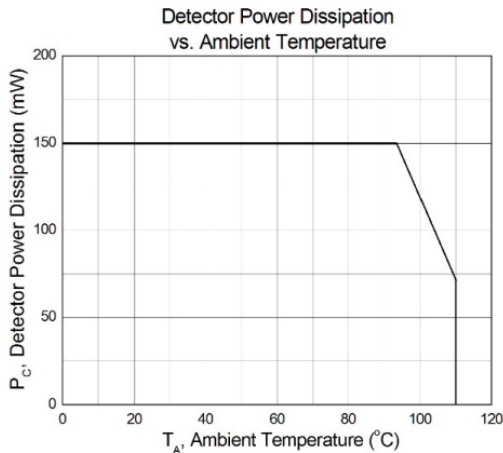


Figure 3

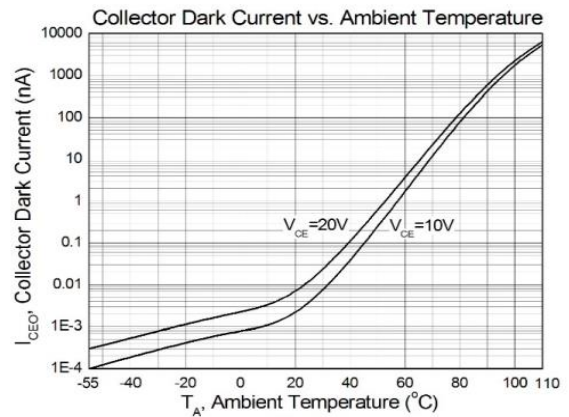


Figure 4

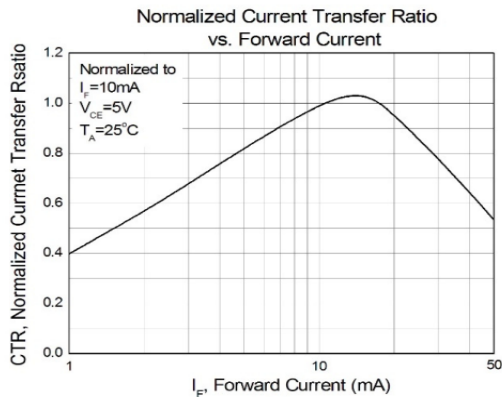


Figure 5

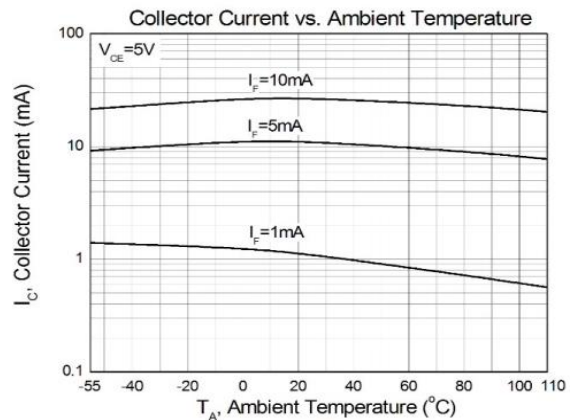


Figure 6

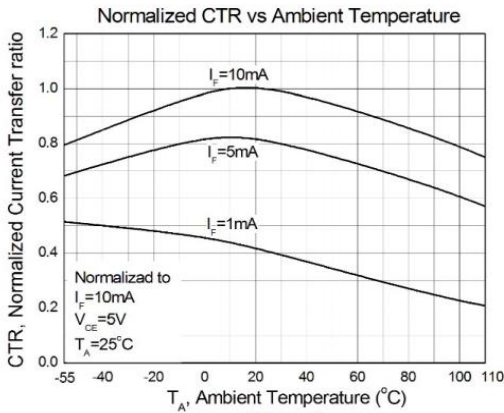


Figure 7

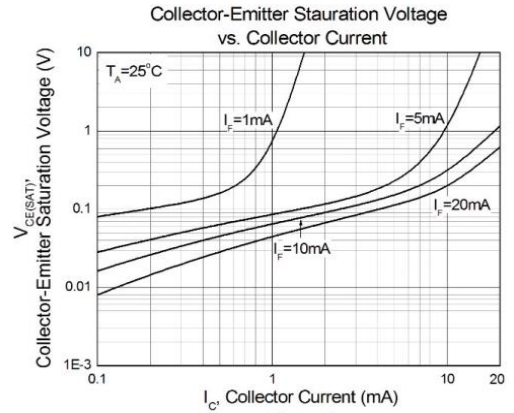


Figure 8

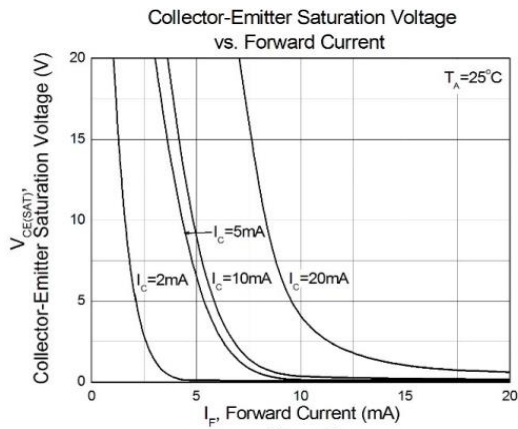


Figure 9

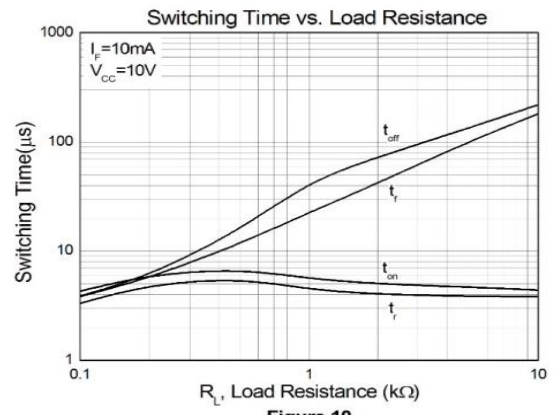


Figure 10

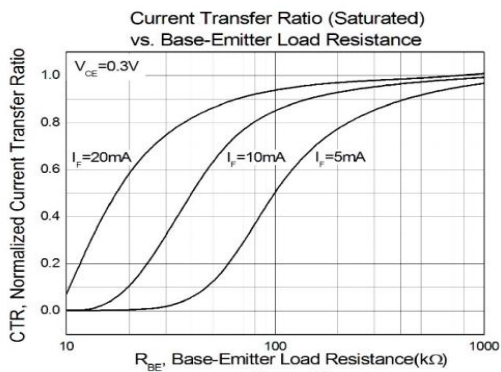


Figure 11

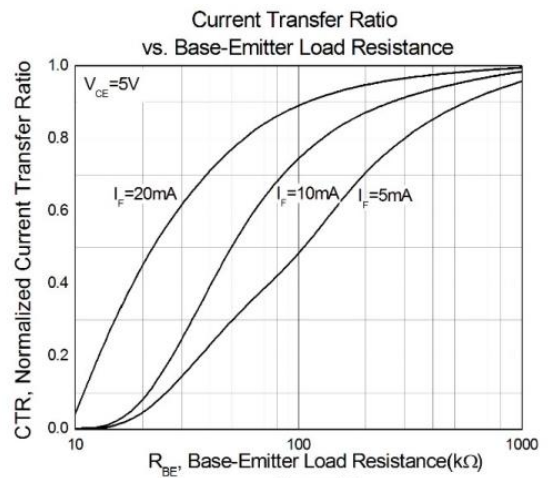


Figure 12

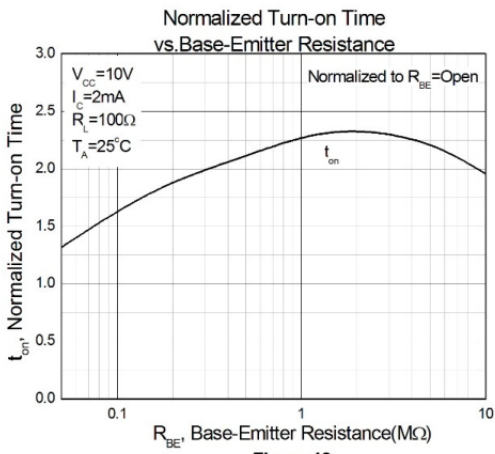


Figure 13

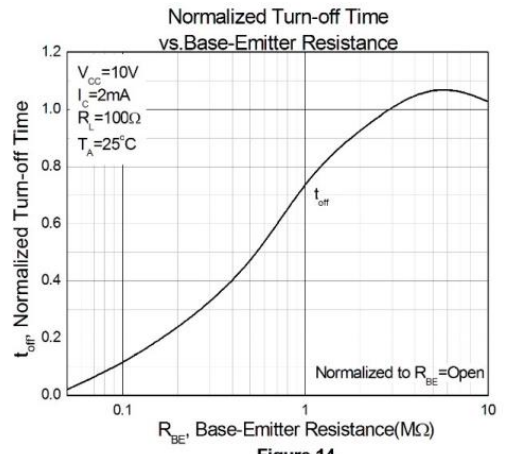
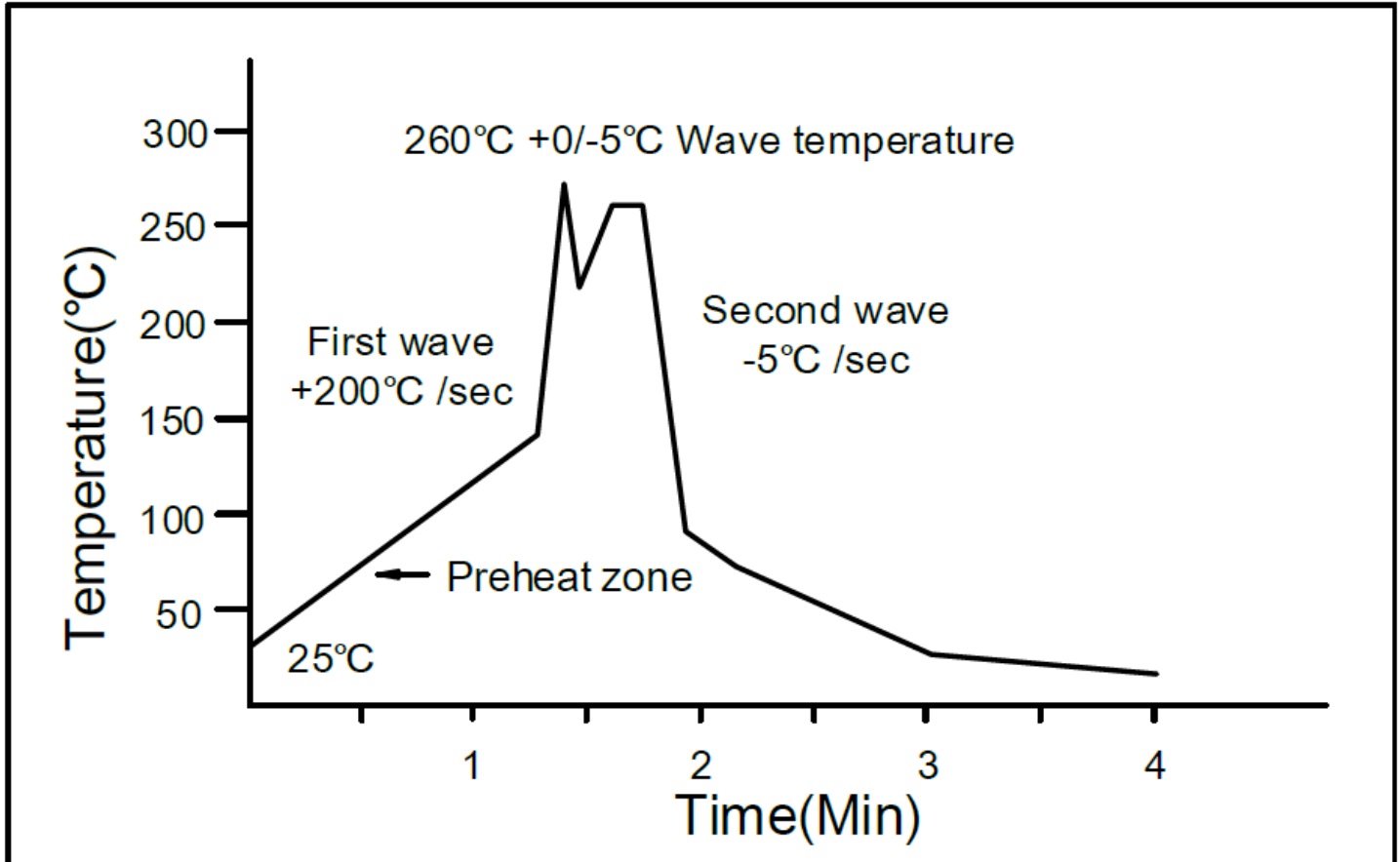


Figure 14

Solder Profile & Footprint**Recommended Wave soldering Profile**

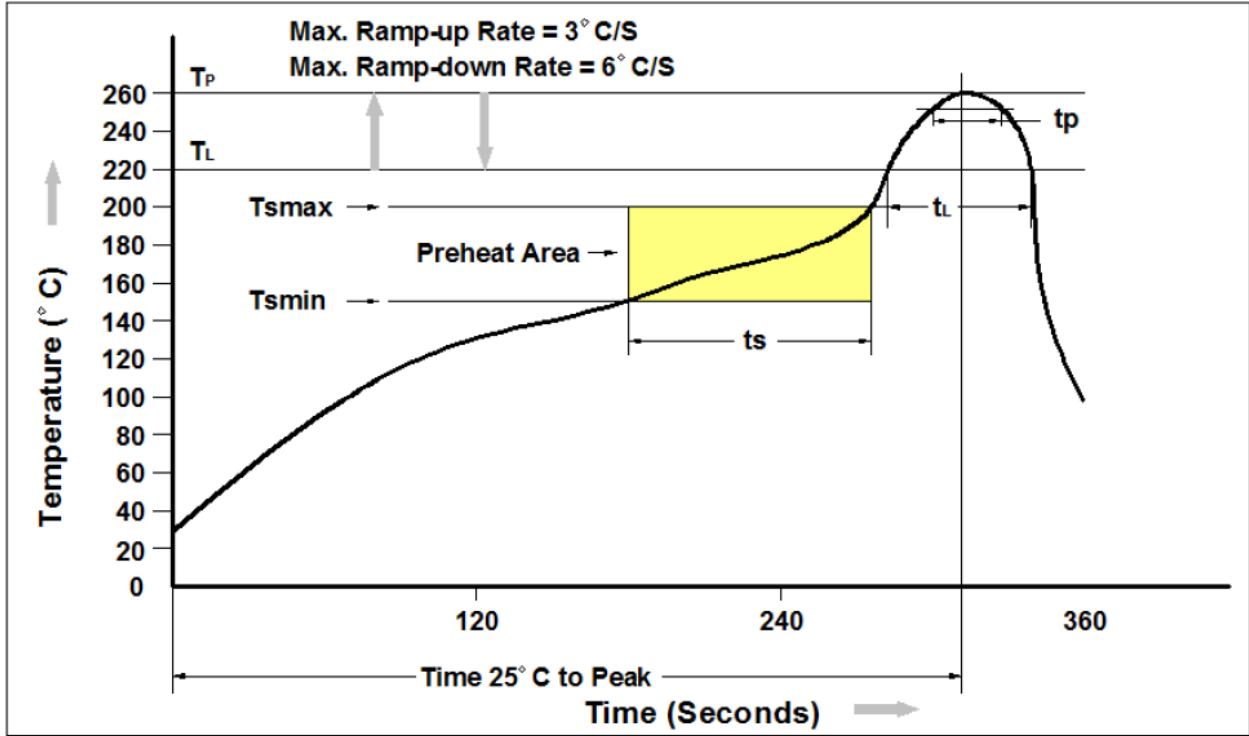
Temperature: 260 +0/-5 °C

Time: 10 sec

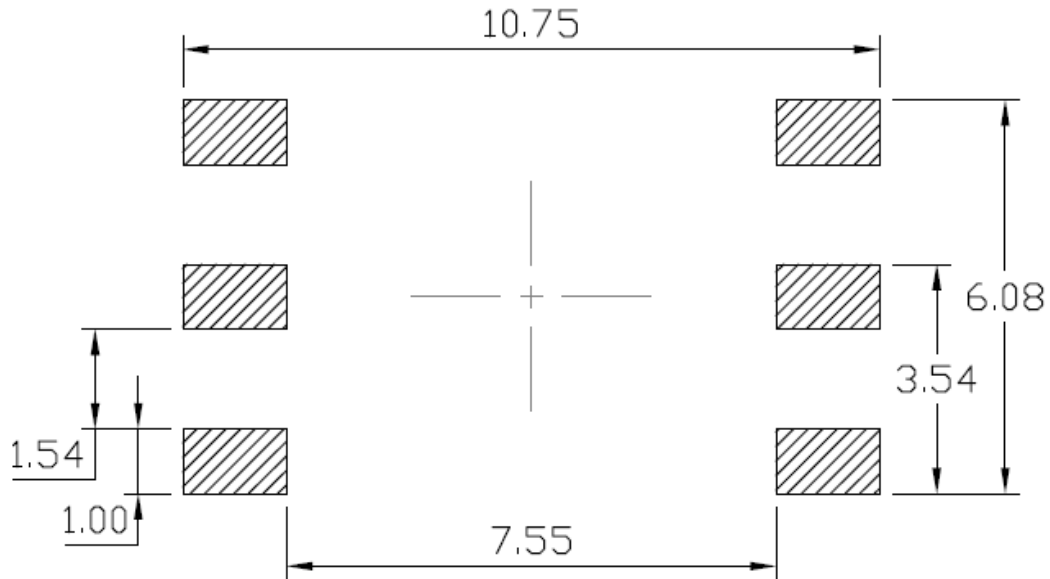
Preheat temperature: 25 to 140 °C

Preheat time: 30 to 80 sec.

Recommended Reflow soldering Profile



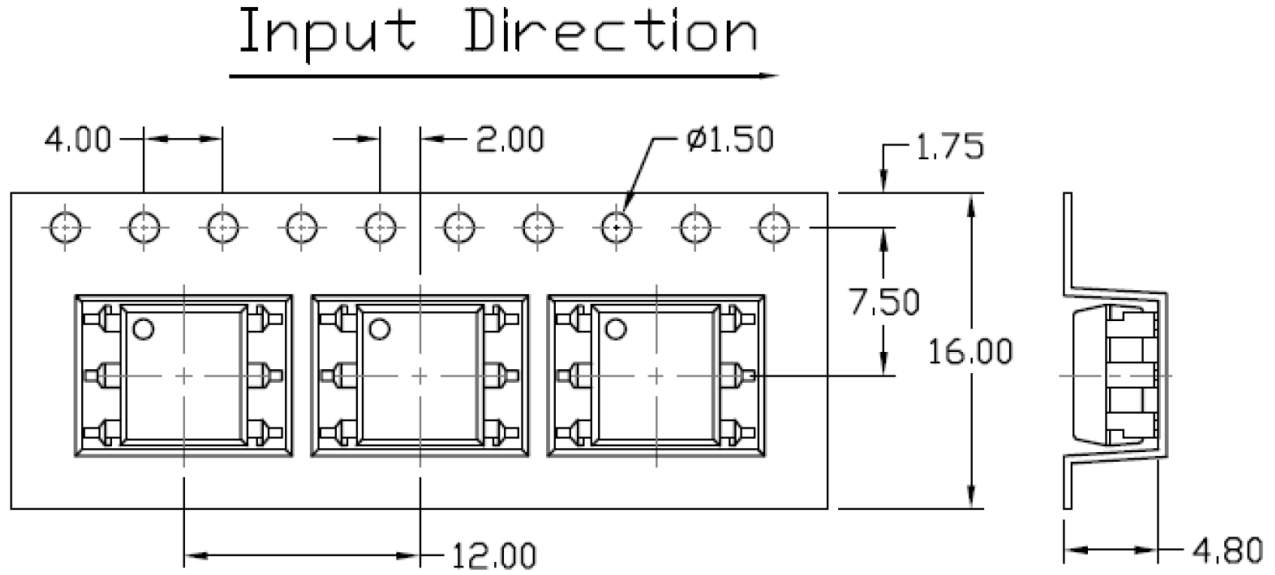
Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmín)	150°C
Temperature Max. (Tsmáx)	200°C
Time (ts) from (Tsmín to Tsmáx)	60-120 seconds
Ramp-up Rate (tL to tp)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (tp) within 5°C of 260°C	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

Solder Profile & Footprint**Recommended Solder Pattern for SMD**

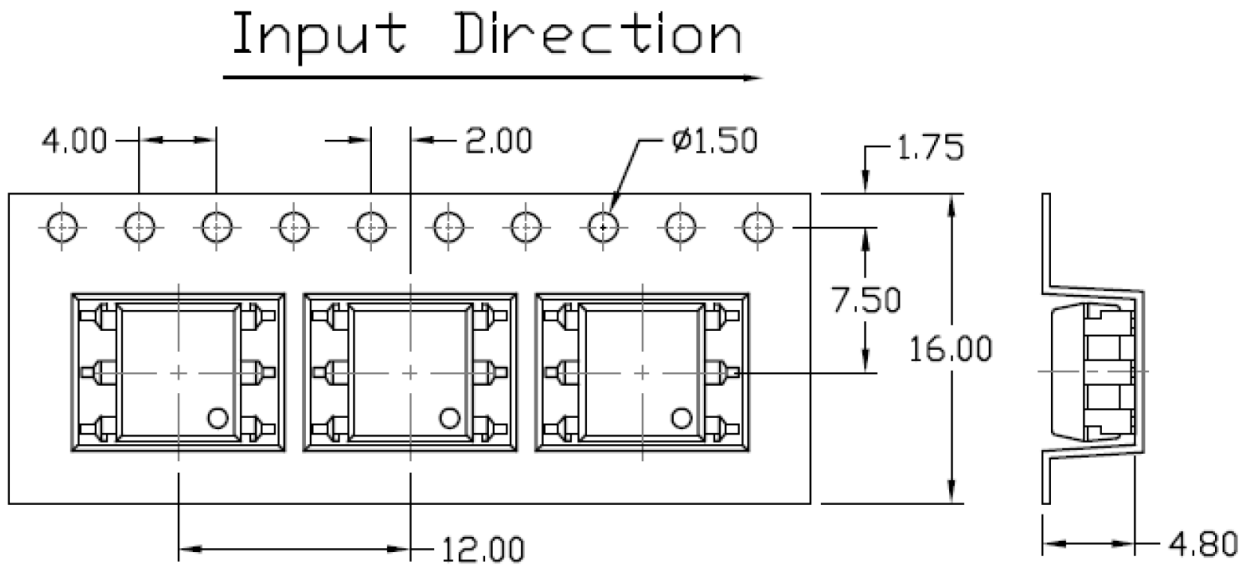
Units: mm

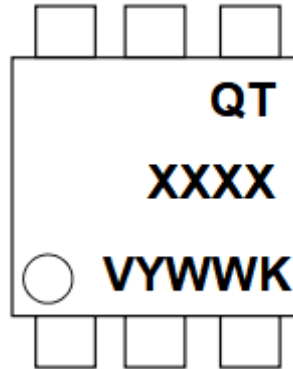
Packing & Labeling

Option 1: ST1 & SLT1



Option 2: ST2 & SLT2



Device Marking**Example**

QT = QT-Brightek Corporation

XXXX = Part Number (4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38, H11A1, H11A2, H11A3, H11A4, H11A5)

V = VDE Option

WW = Week

K = Manufacturing code

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Ordering Information

4N2XVYZ, 4N3XVYZ

X = Part number (X=5, 6, 7 or 8)

V = VDE option (V or None)

Y = Lead form option (S, SL, M or none)

Z = Tape and reel option (T1 or T2 or none)

H11AXVYZ

X = Part number (X=1, 2, 3, 4 or 5)

V = VDE option (V or None)

Y = Lead form option (S, SL, M or none)

Z = Tape and reel option (T1 or T2 or none)

Option	Description	Quantity
None	Standard 6-Pin DIP	50 units/tube
M	Gullwing Lead Bend	50 units/tube
ST1	Surface Mount Lead Forming – with Option 1 Taping	1000 pcs/ reel
ST2	Surface Mount Lead Forming – with Option 2 Taping	1000 pcs/ reel
SLT1	SMD (Low Profile) Lead Forming – with Option 1 Taping	1000 pcs/ reel
SLT2	SMD (Low Profile) Lead Forming – with Option 2 Taping	1000 pcs/ reel

Revision History

Description:	Revision #	Revision Date
Initial release of 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38, H11A1, H11A2, H11A3, H11A4, H11A5 series	1.0	4/27/2010
Feature, certification & compliance and ordering information updates	1.1	02/01/2011
Update specs, format, and packing method	2.0	02/28/2018

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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